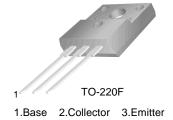


## **KSB1023**

### **Power Amplifier Applications**

- High DC Current Gain
- Low Collector-Emitter Saturation Voltage
- Complement to KSD1413



## **PNP Silicon Darlington Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	- 60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	- 40	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 5	V
I <sub>C</sub>	Collector Current (DC)	- 3	Α
I <sub>CP</sub>	Collector Current (Pulse)	- 6	Α
I <sub>B</sub>	Base Current	- 0.3	Α
P <sub>C</sub>	Collector Dissipation (T <sub>a</sub> =25°C)	2	W
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	20	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### **Electrical Characteristics** $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = -25 \text{mA}, I_B = 0$	- 40			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -60V, I_{E} = 0$			- 20	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 2.5	mA
h <sub>FE1</sub>	DC Current Gain	V <sub>CE</sub> = - 2V, I <sub>C</sub> = - 1A V <sub>CE</sub> = - 2V, I <sub>C</sub> = - 3A	2000 1000			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = -2A, I_B = -4mA$			- 1.5	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = -2A, I_B = -4mA$			- 2	V
t <sub>ON</sub>	Turn ON Time	$V_{CC} = -30V, I_{C} = -3A$		0.3		μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = -6 \text{mA}$		0.6		μs
t <sub>F</sub>	Fall Time	$R_L = 10\Omega$		0.25		μs

# **Typical Characteristics**

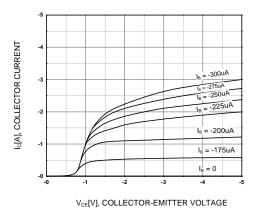


Figure 1. Static Characteristic

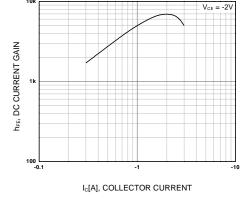


Figure 2. DC current Gain

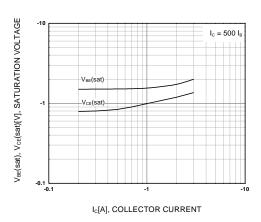


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturating Voltage

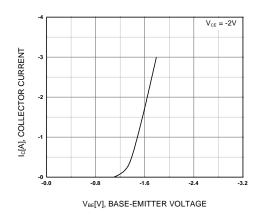


Figure 4. Base-Emitter On Voltage

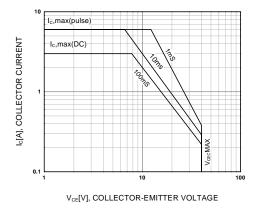


Figure 5. Safe Operating Area

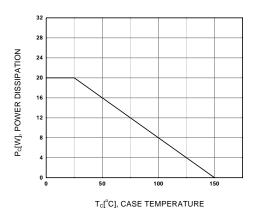
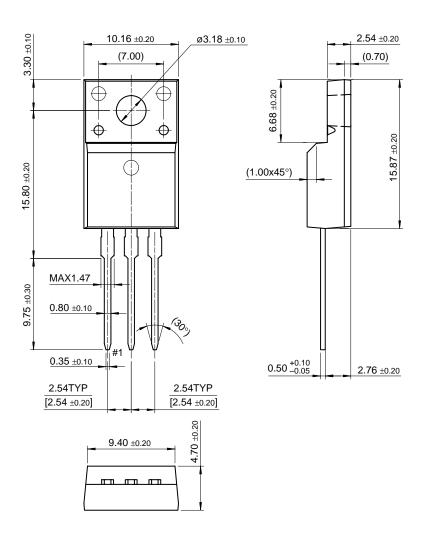


Figure 6. Power Derating

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# **Package Demensions**

# TO-220F



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